Power MOSFET

6 A, 20 V, P-Channel SOIC-8, Dual

Features

- Ultra Low R_{DS(on)}
- Higher Efficiency Extending Battery Life
- Logic Level Gate Drive
- Miniature Dual SOIC-8 Surface Mount Package
- Diode Exhibits High Speed, Soft Recovery
- Avalanche Energy Specified
- These Devices are Pb-Free and are RoHS Compliant
- NVMD Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable

Applications

• Power Management in Portable and Battery–Powered Products, i.e.: Cellular and Cordless Telephones, and PCMCIA Cards

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V _{DSS}	-20	V
Gate-to-Source Voltage - Continuous		±12	V
Thermal Resistance –	V _{GS}	± 12	V
Junction-to-Ambient (Note 1) Total Power Dissipation @ T _A = 25°C Continuous Drain Current @ T _A = 25°C Continuous Drain Current @ T _A = 70°C Maximum Operating Power Dissipation Maximum Operating Drain Current Pulsed Drain Current (Note 4)	R _{θJA} P _D I _D I _D I _{DM}	62.5 2.0 -7.8 -5.7 0.5 -3.89 -40	°C/W W A A W A A
Thermal Resistance – Junction-to-Ambient (Note 2) Total Power Dissipation @ T _A = 25°C Continuous Drain Current @ T _A = 25°C Continuous Drain Current @ T _A = 70°C Maximum Operating Power Dissipation Maximum Operating Drain Current Pulsed Drain Current (Note 4)	R _{θJA} P _D I _D I _D I _D I _{DM}	98 1.28 -6.2 -4.6 0.3 -3.01 -35	°C/W W A A W A
Thermal Resistance – Junction–to–Ambient (Note 3) Total Power Dissipation @ T _A = 25°C Continuous Drain Current @ T _A = 25°C Continuous Drain Current @ T _A = 70°C Maximum Operating Power Dissipation Maximum Operating Drain Current Pulsed Drain Current (Note 4) Operating and Storage Temperature Range	R _{θJA} P _D I _{DM}	166 0.75 -4.8 -3.5 0.2 -2.48 -30	°C/W W A A W A A
Single Pulse Drain–to–Source Avalanche Energy – Starting $T_J = 25^{\circ}\text{C}$ ($V_{DD} = -20$ Vdc, $V_{GS} = -5.0$ Vdc, Peak $I_L = -5.0$ Apk, $L = 40$ mH, $R_G = 25~\Omega$)	E _{AS}	+150 500	mJ
Maximum Lead Temperature for Soldering Purposes for 10 seconds	TL	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

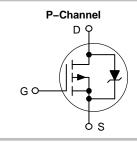
- 1. Mounted onto a 2" square FR-4 Board (1 in sq, 2 oz. Cu 0.06" thick single sided), t = 10 seconds.
- 2. Mounted onto a 2" square FR-4 Board (1 in sq, 2 oz. Cu 0.06" thick single sided), t = steady state.
- 3. Minimum FR-4 or G-10 PCB, t = steady state.
- 4. Pulse Test: Pulse Width = $300 \mu s$, Duty Cycle = 2%.



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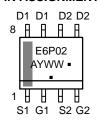
www.onsemi.com

6 AMPERES, 20 VOLTS



MARKING DIAGRAM & PIN ASSIGNMENT





E6P02 = Specific Device Code A = Assembly Location

Y = Year WW = Work Week ■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
LITH I DODOOD OO	_	
NTMD6P02R2G	SOIC-8 (Pb-Free)	2500 / Tape & Reel
NVMD6P02R2G	SOIC-8 (Pb-Free)	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)*

Cha	racteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltag	e	V _{(BR)DSS}	20			Vdc
(V _{GS} = 0 Vdc, I _D = -250 μAdc) Temperature Coefficient (Positive)			–20 –	-11.6	_	mV/°C
Zero Gate Voltage Drain Current (V _{DS} = -20 Vdc, V _{GS} = 0 Vdc, T, (V _{DS} = -20 Vdc, V _{GS} = 0 Vdc, T,		I _{DSS}	_ _	_ _	-1.0 -5.0	μAdc
Gate–Body Leakage Current (V _{GS} = -12 Vdc, V _{DS} = 0 Vdc)		I _{GSS}	-	_	-100	nAdc
Gate-Body Leakage Current (V _{GS} = +12 Vdc, V _{DS} = 0 Vdc)		I _{GSS}	-	_	100	nAdc
ON CHARACTERISTICS				•	•	•
Gate Threshold Voltage $(V_{DS} = V_{GS}, I_{D} = -250 \mu Adc)$ Temperature Coefficient (Negative)		V _{GS(th)}	-0.6 -	-0.88 2.6	-1.20 -	Vdc mV/°C
Static Drain-to-Source On-State R (V_{GS} = -4.5 Vdc, I_D = -6.2 Adc) (V_{GS} = -2.5 Vdc, I_D = -5.0 Adc) (V_{GS} = -2.5 Vdc, I_D = -3.1 Adc)	esistance	R _{DS(on)}		0.027 0.038 0.038	0.033 0.050 -	Ω
Forward Transconductance (V _{DS} = -	$-10 \text{ Vdc}, I_D = -6.2 \text{ Adc})$	9FS	-	15	_	Mhos
DYNAMIC CHARACTERISTICS						
Input Capacitance		C _{iss}	_	1380	1700	pF
Output Capacitance	$(V_{DS} = -16 \text{ Vdc}, V_{GS} = 0 \text{ Vdc}, $ f = 1.0 MHz)	C _{oss}	1	515	775	
Reverse Transfer Capacitance	,	C _{rss}	-	250	450	<u>]</u>
SWITCHING CHARACTERISTICS (Notes 5 and 6)					
Turn-On Delay Time		t _{d(on)}	_	15	25	ns
Rise Time	(V _{DD} = -10 Vdc, I _D = -1.0 Adc, V _{GS} = -10 Vdc,	t _r	1	20	50	
Turn-Off Delay Time	$R_G = 6.0 \Omega$)	t _{d(off)}	1	85	125	
Fall Time		t _f	-	50	110	
Turn-On Delay Time		t _{d(on)}	-	17	-	ns
Rise Time	$(V_{DD} = -16 \text{ Vdc}, I_D = -6.2 \text{ Adc},$	t _r	-	65	-	
Turn-Off Delay Time	$V_{GS} = -4.5 \text{ Vdc},$ $R_G = 6.0 \Omega)$	t _{d(off)}	_	50	-	
Fall Time		t _f	_	80	-	
Total Gate Charge	(V _{DS} = -16 Vdc,	Q _{tot}	_	20	35	nC
Gate-Source Charge	$V_{GS} = -4.5 \text{ Vdc},$	Q _{gs}	_	4.0	-	
Gate-Drain Charge	I _D = -6.2 Adc)	Q _{gd}	-	8.0	-	
BODY-DRAIN DIODE RATINGS (No	ote 5)					
Diode Forward On-Voltage	$(I_S = -1.7 \text{ Adc}, V_{GS} = 0 \text{ Vdc})$ $(I_S = -1.7 \text{ Adc}, V_{GS} = 0 \text{ Vdc}, T_J = 125^{\circ}\text{C})$	V _{SD}	- -	-0.80 -0.65	-1.2 -	Vdc
Diode Forward On–Voltage	$(I_S = -6.2 \text{ Adc}, V_{GS} = 0 \text{ Vdc})$ $(I_S = -6.2 \text{ Adc}, V_{GS} = 0 \text{ Vdc}, T_J = 125^{\circ}\text{C})$	V _{SD}	- -	-0.95 -0.80	_ _	Vdc
Reverse Recovery Time		t _{rr}	-	50	80	ns
	$(I_S = -1.7 \text{ Adc}, V_{GS} = 0 \text{ Vdc}, \\ dI_S/dt = 100 \text{ A/}\mu\text{s})$	t _a	-	20	-	
	3 3 3 3 3 3 3 3 3 3 3 3 3 3 3 3 3 3 3 3	t _r	_	30	_	
Reverse Recovery Stored Charge		Q _{RR}	_	0.04	_	μС

^{5.} Indicates Pulse Test: Pulse Width = 300 μs max, Duty Cycle = 2%.
6. Switching characteristics are independent of operating junction temperature.

^{*}Handling precautions to protect against electrostatic discharge are mandatory.

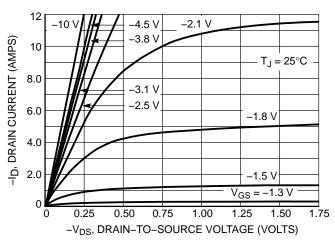


Figure 1. On-Region Characteristics

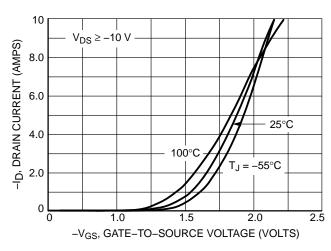


Figure 2. Transfer Characteristics

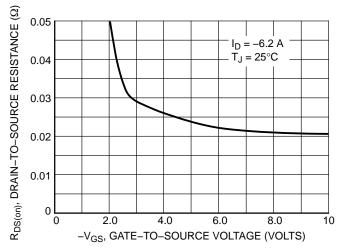


Figure 3. On–Resistance versus Gate–To–Source Voltage

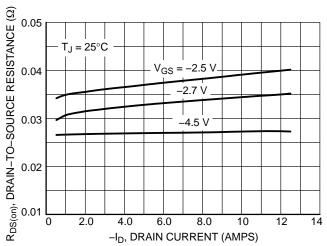


Figure 4. On-Resistance versus Drain Current and Gate Voltage

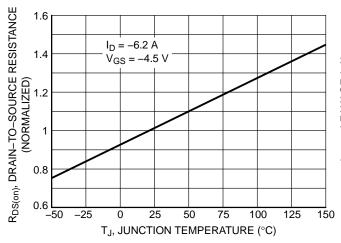


Figure 5. On–Resistance Variation with Temperature

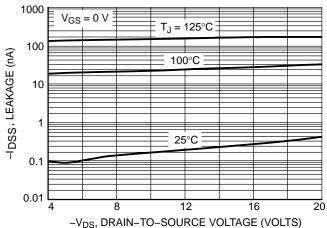
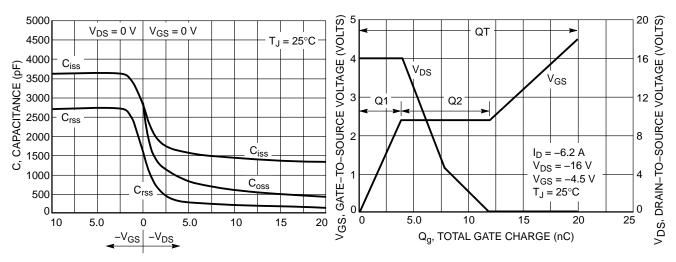


Figure 6. Drain-To-Source Leakage Current versus Voltage



GATE-TO-SOURCE OR DRAIN-TO-SOURCE VOLTAGE (VOLTS)

Figure 7. Capacitance Variation

Figure 8. Gate-To-Source and Drain-To-Source Voltage versus Total Charge

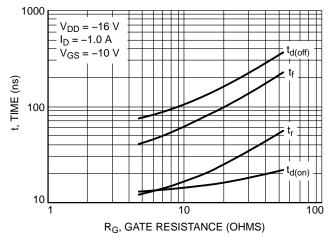


Figure 9. Resistive Switching Time Variation versus Gate Resistance

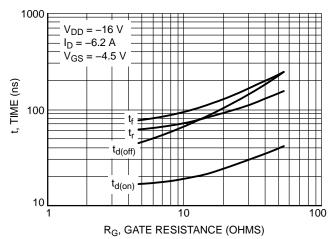


Figure 10. Resistive Switching Time Variation versus Gate Resistance

DRAIN-TO-SOURCE DIODE CHARACTERISTICS

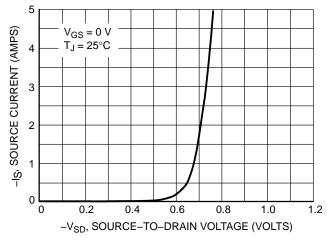


Figure 11. Diode Forward Voltage versus Current

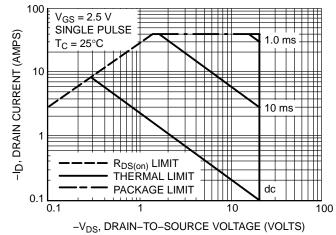


Figure 12. Maximum Rated Forward Biased Safe Operating Area

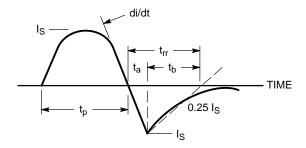


Figure 13. Diode Reverse Recovery Waveform

TYPICAL ELECTRICAL CHARACTERISTICS

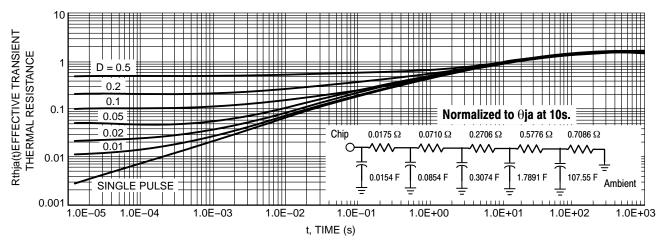
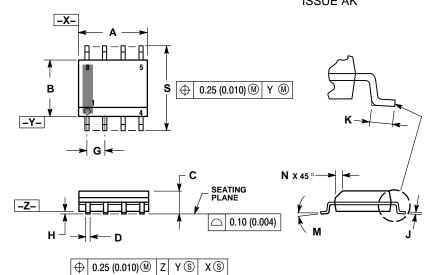


Figure 14. Thermal Response

PACKAGE DIMENSIONS

SOIC-8 NB CASE 751-07 ISSUE AK



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: MILLIMETER.
 DIMENSION A AND B DO NOT INCLUDE
- DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
 MAXIMUM MOLD PROTRUSION 0.15 (0.006)
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
 DIMENSION D DOES NOT INCLUDE DAMBAR
- DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
- MAXIMUM MATERIAL CONDITION. 6. 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.80	5.00	0.189	0.197
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
Н	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
М	0 °	8 °	0 °	8 °
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

STYLE 11:

- PIN 1. SOURCE 1
 - 2. GATE 1
 - 3. SOURCE 2 4. GATE 2
 - 5. DRAIN 2
 - 6. DRAIN 2
 - 7. DRAIN 1 8. DRAIN 1

(mm inches)

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

SOLDERING FOOTPRINT

7.0

0.275

0.6

1.52

0.060

4.0

0.155

1.270

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